

UNISONIC TECHNOLOGIES CO., LTD

25N10 **Preliminary Power MOSFET**

N-CHANNEL ENHANCEMENT MODE POWER MOSFET

DESCRIPTION

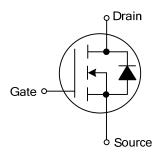
The UTC 25N10 is an N-channel enhancement mode power MOSFET and it uses UTC's perfect technology to provide designers with fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

It is generally suitable for all commercial-industrial applications and DC/DC converters requiring low voltage.

FEATURES

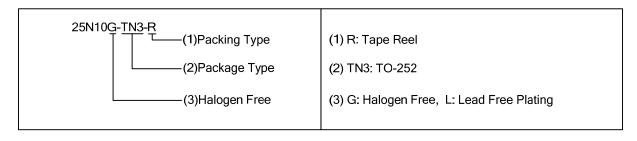
- * Single Drive Requirement
- * Low Gate Charge
- * RoHS Compliant

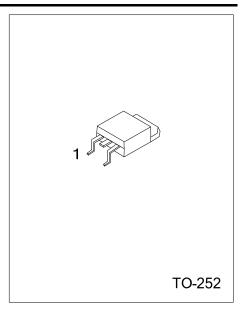
SYMBOL



ORDERING INFORMATION

Ordering Number		Dookono	Pin Assignment			Dealine	
Lead Free Plating	Halogen Free	Package	1	2	3	Packing	
25N10L-TN3-R	25N10G-TN3-R	TO-252	G	D	S	Tape Reel	





■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Drain Source Voltage		V_{DSS}	100	٧
Gate Source Voltage		V_{GSS}	±20	٧
Continuous Drain Current (V _{GS} =10V	T _C =25°C	I_{D}	23	Α
Continuous Diain Current (VGS=10V)	T _C = 100°C	I_D	14.6	Α
Pulsed Drain Current (Note 2)		I _{DM}	80	Α
Total Power Dissipation (T _C =25°C)		P_D	41	W
Operating Junction Temperature		TJ	-55 ~ +150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	100	°C/W
Junction to Case	θ_{JC}	3	°C/W

■ **ELECTRICAL CHARACTERISTICS** (T_J=25°C, unless otherwise specified)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT			
OFF CHARACTERISTICS								
BV _{DSS}	$V_{GS} = 0V$, $I_D = 1mA$	100			V			
ΔBV _{DSS} /ΔT _J	Reference to 25°C , I _D =1mA		0.14		V/°C			
I _{DSS}	V _{DS} =100V, V _{GS} =0V, T _J =25°C V _{DS} =80V, V _{GS} =0V,T _J =150°C			25 100	μA μA			
I _{GSS}	1			±100	nA			
Gate-Source Leakage Current I _{GSS} V _{GS} =±20V ±100 nA ON CHARACTERISTICS								
$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$			4	V			
R _{DS(ON)}	V _{GS} =10V, I _D =16A			80	mΩ			
g fs	V _{DS} =10V, I _D =16A		14		S			
DYNAMIC PARAMETERS								
C _{ISS}			1060	1700	pF			
Coss			270		pF			
C _{RSS}			8		pF			
R_G	f=1.0MHz		1.5	2.3	Ω			
Q_G			19	30	nC			
Q_GS	V_{GS} =10V, V_{DS} =80V, I_{D} =16A		5		nC			
Q_GD			6		nC			
t _{D(ON)}			10		ns			
t _R	V_{DD} =50V, I_{D} =16A, R_{G} =3.3 Ω ,		28		ns			
t _{D(OFF)}	V_{GS} =10V, R_{D} =3.125 Ω		17		ns			
t _F	<u>] </u>		2		ns			
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
V_{SD}	I _S =16A, V _{GS} =0V			1.3	V			
t _{RR}	I_S =16A, V_{GS} =0V,		90		ns			
Q_{RR}	dI/dt=100A/μs		380		nC			
	BVDSS ABVDSS/ATJ IDSS IGSS VGS(TH) RDS(ON) GFS COSS CRSS RG QG QGS QGD tD(ON) tR tD(OFF) tF CHARACTERIS VSD tRR	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{ c c c c c c } \hline BV_{DSS} & V_{GS} = 0V, \ I_D = 1mA & 100 & \\ \hline \Delta BV_{DSS}/\Delta T_J & Reference to 25^{\circ}C \ , \ I_D = 1mA & 0.14 & \\ \hline I_{DSS} & V_{DS} = 100V, \ V_{GS} = 0V, \ T_J = 25^{\circ}C & 25 \\ \hline V_{DS} = 80V, \ V_{GS} = 0V, \ T_J = 150^{\circ}C & 100 \\ \hline I_{GSS} & V_{GS} = \pm 20V & \pm 100 & \\ \hline \hline V_{GS(TH)} & V_{DS} = V_{GS}, \ I_D = 250\mu A & 2 & 4 \\ \hline R_{DS(ON)} & V_{GS} = 10V, \ I_D = 16A & 80 \\ \hline g_{FS} & V_{DS} = 10V, \ I_D = 16A & 14 & \\ \hline \hline \hline C_{ISS} & \\ \hline C_{OSS} & V_{DS} = 25V, \ V_{GS} = 0V, \ f = 1.0MHz & 1.5 & 2.3 \\ \hline \hline \hline Q_G & V_{GS} = 10V, \ V_{DS} = 80V, \ I_D = 16A & 5 \\ \hline Q_{GD} & V_{GS} = 10V, \ V_{DS} = 80V, \ I_D = 16A & 5 \\ \hline Q_{GD} & V_{GS} = 10V, \ V_{DS} = 80V, \ I_D = 16A & 5 \\ \hline Q_{GD} & I_D = 16A, \ R_G = 3.3\Omega, & 28 \\ \hline t_{D(OFF)} & V_{GS} = 10V, \ R_D = 3.125\Omega & 17 \\ \hline t_F & 2 & 2 \\ \hline \hline \mathcal{C} HARACTERISTICS & 0 & 1.3 \\ \hline Q_{RR} & I_S & = 16A, V_{GS} & = 0V, & 90 \\ \hline Q_{RR} & dI/dt = 100A/\mu s & 380 \\ \hline \hline \end{array}$			

Note: Pulse Test : Pulse width ≤ 300µs, Duty cycle ≤ 2%

^{2.} Pulse width limited by max. junction temperature

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